# **ECH8695R**



http://onsemi.com

## N-Channel Power MOSFET 24V, 11A, 9.1mΩ, Dual ECH8 Common Drain

#### **Features**

- Low On-resistance
- 2.5V drive
- Common-drain type
- Protection diode in

- Built-in gate protection resistor
- Best suited for LiB charging and discharging switch
- Halogen free compliance

### **Specifications**

**Absolute Maximum Ratings** at Ta = 25°C

| Parameter               | Symbol           | Conditions   | Value        | Unit |
|-------------------------|------------------|--|--------------|------|
| Drain to Source Voltage | V <sub>DSS</sub> |  | 24           | V    |
| Gate to Source Voltage  | VGSS             |  | ±12.5        | V    |
| Drain Current (DC)      | ID               |  | 11           | Α    |
| Drain Current (Pulse)   | I <sub>DP</sub>  | PW≤10μs, duty cycle≤1%   | 60           | Α    |
| Power Dissipation       | PD               | When mounted on ceramic substrate(900mm <sup>2</sup> ×0.8mm) 1unit | 1.4          | W    |
| Total Dissipation       | PT               | When mounted on ceramic substrate(900mm <sup>2</sup> ×0.8mm)       | 1.5          | W    |
| Junction Temperature    | Tj               |  | 150          | °C   |
| Storage Temperature     | Tstg             |  | - 55 to +150 | °C   |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **Thermal Resistance Ratings**

| Parameter   | Symbol          | Value | Unit  |
|---|-----------------|-------|-------|
| Junction to Ambient   | Po              | 89.3  | °C /W |
| When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm) 1unit | $R_{\theta JA}$ | 09.3  | C /vv |

#### **Electrical Characteristics** at Ta = 25°C

| Parameter                                  | Symbol                | Conditions                                  | Value |     |      |      |
|--|-----------------------|---|-------|-----|------|------|
|  |                       |   | min   | typ | max  | Unit |
| Drain to Source Breakdown Voltage          | V(BR)DSS              | I <sub>D</sub> =1mA, V <sub>GS</sub> =0V    | 24    |     |      | ٧    |
| Zero-Gate Voltage Drain Current            | IDSS                  | V <sub>DS</sub> =20V, V <sub>GS</sub> =0V   |       |     | 1    | μΑ   |
| Gate to Source Leakage Current             | IGSS                  | VGS=±8V, VDS=0V                             |       |     | ±1   | μΑ   |
| Gate Threshold Voltage                     | VGS(th)               | V <sub>DS</sub> =10V, I <sub>D</sub> =1mA   | 0.5   |     | 1.3  | ٧    |
| Forward Transconductance                   | gFS .                 | V <sub>DS</sub> =10V, I <sub>D</sub> =5A    |       | 6.5 |      | S    |
| Static Drain to Source On-State Resistance | R <sub>DS</sub> (on)1 | I <sub>D</sub> =5A, V <sub>GS</sub> =4.5V   | 5.6   | 7.0 | 9.1  | mΩ   |
|  | R <sub>DS</sub> (on)2 | I <sub>D</sub> =5A, V <sub>GS</sub> =4.0V   | 5.8   | 7.3 | 9.5  | mΩ   |
|  | R <sub>DS</sub> (on)3 | I <sub>D</sub> =5A, V <sub>GS</sub> =3.1V   | 6.5   | 8.2 | 11.5 | mΩ   |
|  | R <sub>DS</sub> (on)4 | I <sub>D</sub> =2.5A, V <sub>GS</sub> =2.5V | 7.6   | 9.5 | 13.3 | mΩ   |

Continued on next page.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

## **ECH8695R**

Continued from preceding page.

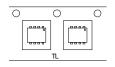
| Parameter                     | Completel            | Conditions   | Value |       |     | 11.7 |
|-------------------------------|----------------------|--|-------|-------|-----|------|
|                               | Symbol               |  | min   | typ   | max | Unit |
| Turn-ON Delay Time            | t <sub>d</sub> (on)  | See specified Test Circuit.                                      |       | 300   |     | ns   |
| Rise Time                     | t <sub>r</sub>       |  |       | 320   |     | ns   |
| Turn-OFF Delay Time           | t <sub>d</sub> (off) |  |       | 19700 |     | ns   |
| Fall Time                     | t <sub>f</sub>       |  |       | 22300 |     | ns   |
| Total Gate Charge             | Qg                   | V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =11A |       | 10    |     | nC   |
| Gate to Source Charge         | Qgs                  |  |       | 1.6   |     | nC   |
| Gate to Drain "Miller" Charge | Qgd                  |  |       | 1.5   |     | nC   |
| Forward Diode Voltage         | V <sub>SD</sub>      | I <sub>S</sub> =11A, V <sub>GS</sub> =0V                         |       | 0.77  | 1.2 | V    |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **Ordering & Package Information**

| Device        | Package | Shipping             | note                           |
|---------------|---------|----------------------|--------------------------------|
| ECH8695R-TL-W | ECH8    | 3,000<br>pcs. / reel | Pb-Free<br>and<br>Halogen Free |

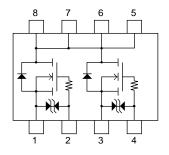
## Packing Type:TL



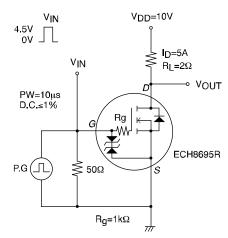
## Marking

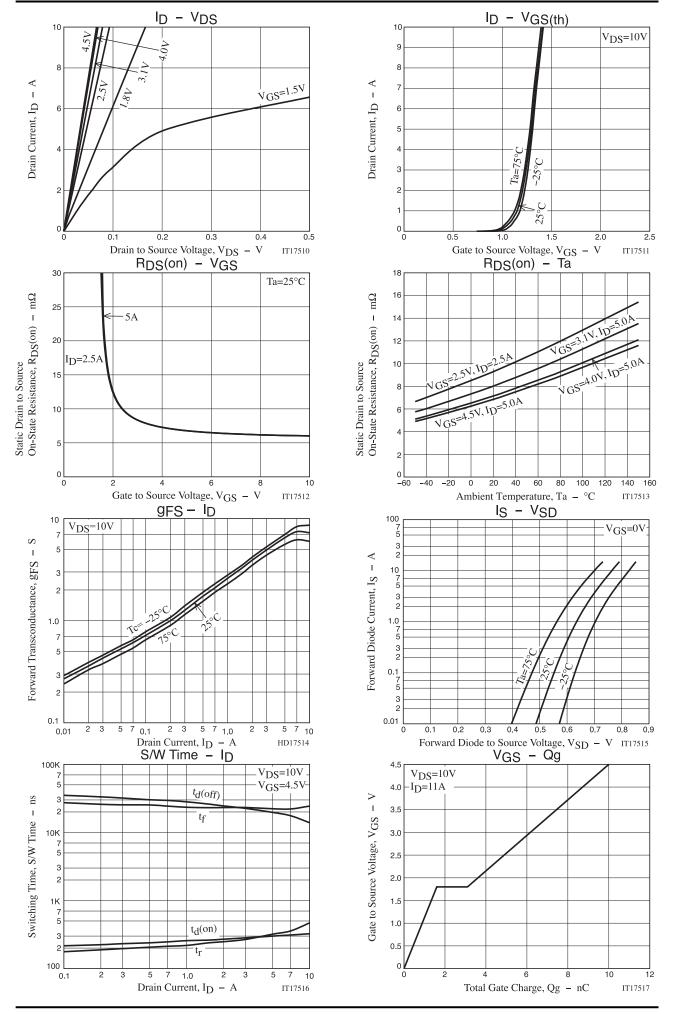


### **Electrical Connection**

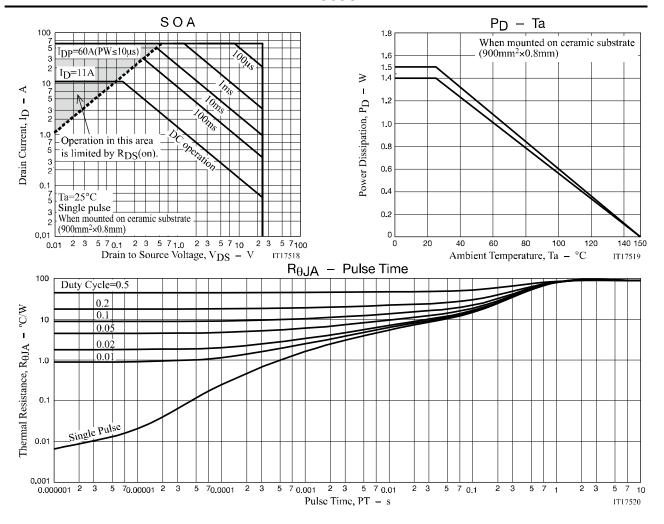


## **Switching Time Test Circuit**



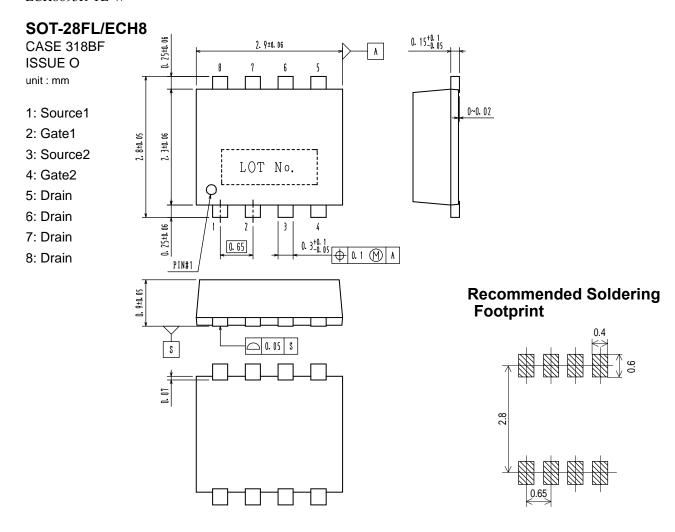


## **ECH8695R**



## **Package Dimensions**

ECH8695R-TL-W



Note on usage: Since the ECH8695R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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